



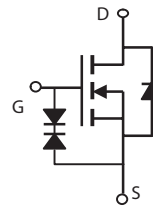
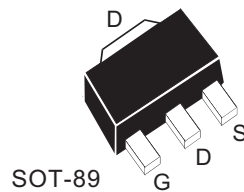
N-Channel Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY

V _{DS}	I _D	R _{DS(ON)} (Ω) Max
100V	1A	1.9 @ V _{GS} =10V
		2.2 @ V _{GS} =4.5V

FEATURES

- Super high dense cell design for low R_{DS(ON)}.
- Rugged and reliable.
- Surface Mount Package.
- ESD Protected.



ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Symbol	Parameter	Limit	Units
V _{DS}	Drain-Source Voltage ^d	100	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current-Continuous	T _A =25°C	1
		T _A =70°C	0.8
I _{DM}	-Pulsed ^a	3.16	A
E _{AS}	Single Pulse Avalanche Energy ^c	1.1	mJ
P _D	Maximum Power Dissipation	T _A =25°C	1.25
		T _A =70°C	0.8
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C

THERMAL CHARACTERISTICS

Symbol	Parameter	Limit	Units
R _{θJA}	Thermal Resistance, Junction-to-Ambient	100	°C/W

STK900

Ver 1.0

ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage ^d	V _{GS} =0V , I _D =10mA	100			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =80V , V _{GS} =0V			1	uA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V , V _{DS} =0V			±10	uA
ON CHARACTERISTICS						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	1	1.7	3	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =10V , I _D =0.5A		1.50	1.90	ohm
		V _{GS} =4.5V , I _D =0.5A		1.75	2.20	ohm
g _{FS}	Forward Transconductance	V _{DS} =10V , I _D =0.5A		0.88		S
DYNAMIC CHARACTERISTICS ^b						
C _{ISS}	Input Capacitance	V _{DS} =25V, V _{GS} =0V f=1.0MHz		64		pF
C _{OSS}	Output Capacitance			17.4		pF
C _{RSS}	Reverse Transfer Capacitance			8.5		pF
SWITCHING CHARACTERISTICS ^b						
t _{D(ON)}	Turn-On Delay Time	V _{DD} =45V I _D =0.5A V _{GS} =10V R _{GEN} = 6 ohm		7.5		ns
t _r	Rise Time			8.5		ns
t _{D(OFF)}	Turn-Off Delay Time			65		ns
t _f	Fall Time			12		ns
Q _g	Total Gate Charge	V _{DS} =45V, I _D =0.5A, V _{GS} =10V		1.9		nC
		V _{DS} =45V, I _D =0.5A, V _{GS} =4.5V		1.23		nC
Q _{gs}	Gate-Source Charge	V _{DS} =45V, I _D =0.5A,		0.43		nC
Q _{gd}	Gate-Drain Charge	V _{GS} =10V		0.62		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =0.1A		0.8	1.3	V
Notes a.Pulse Test:Pulse Width ≤ 300us, Duty Cycle ≤ 2%. b.Guaranteed by design, not subject to production testing. c.Starting T _J =25°C, L=0.5mH, V _{DD} = 40V.(See Figure13) d.Pulse Test:Pulse Width ≤ 1us, Duty Cycle ≤ 1%.						

Jun,22,2011

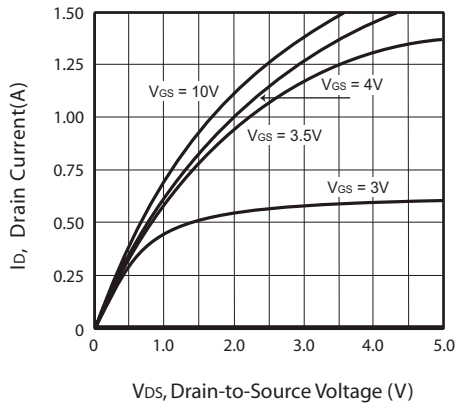


Figure 1. Output Characteristics

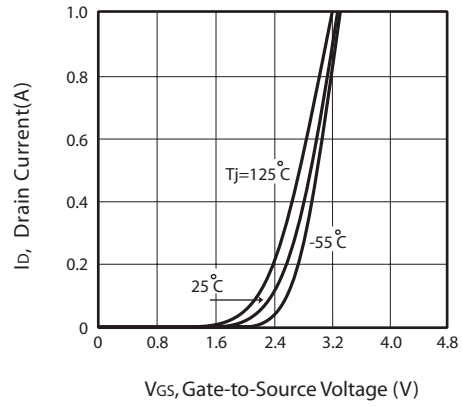


Figure 2. Transfer Characteristics

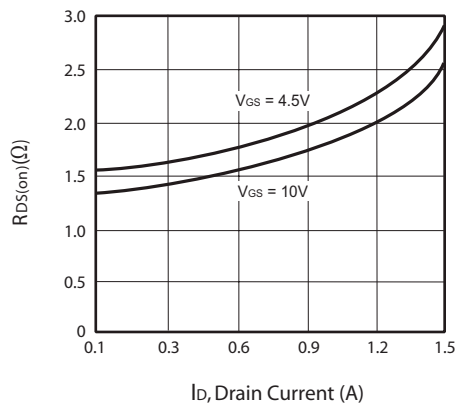


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

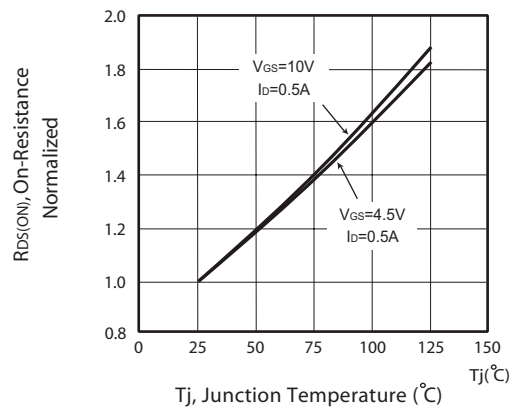


Figure 4. On-Resistance Variation with Drain Current and Temperature

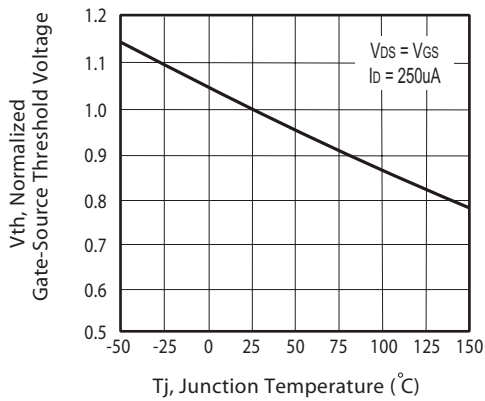


Figure 5. Gate Threshold Variation with Temperature

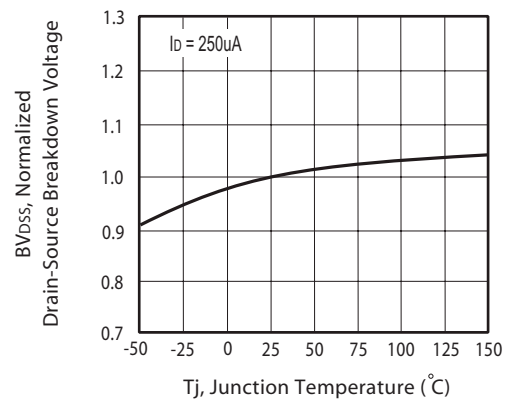


Figure 6. Breakdown Voltage Variation with Temperature

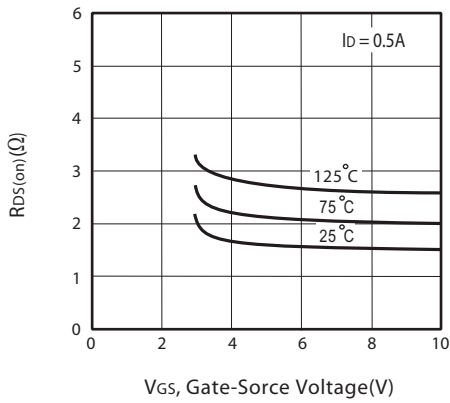


Figure 7. On-Resistance vs. Gate-Source Voltage

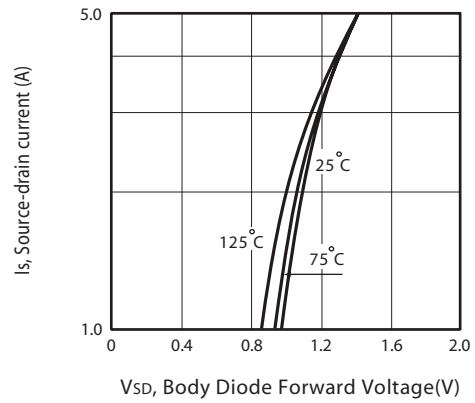


Figure 8. Body Diode Forward Voltage Variation with Source Current

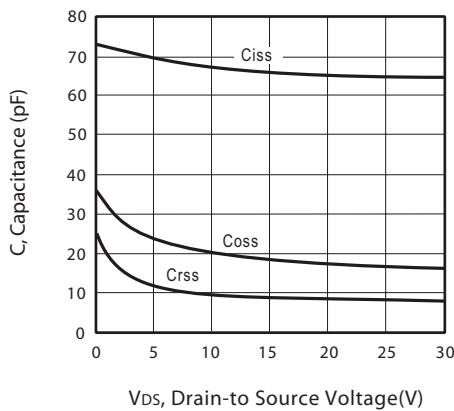


Figure 9. Capacitance

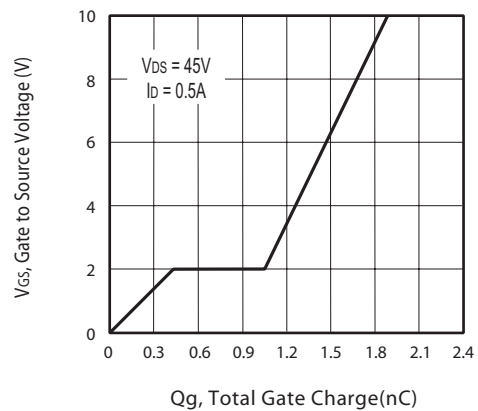


Figure 10. Gate Charge

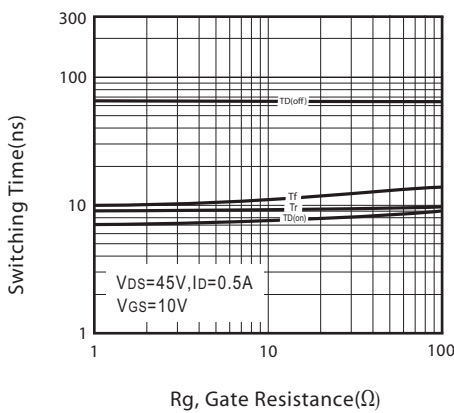


Figure 11. switching characteristics

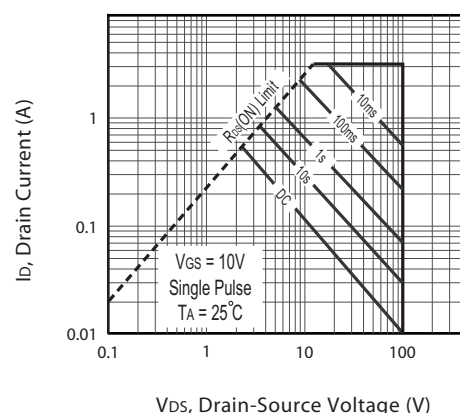
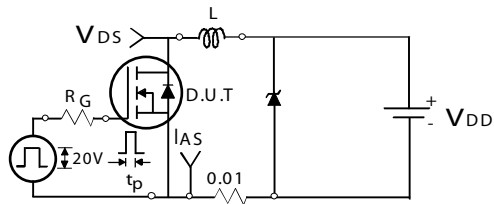
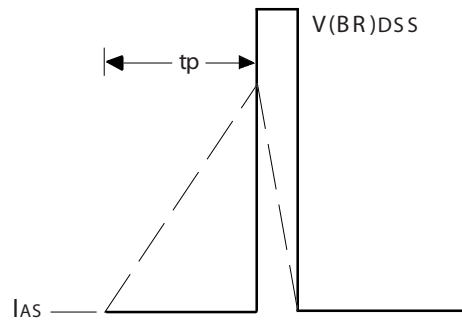


Figure 12. Maximum Safe Operating Area



Unclamped Inductive Test Circuit

Figure 13a.



Unclamped Inductive Waveforms

Figure 13b.

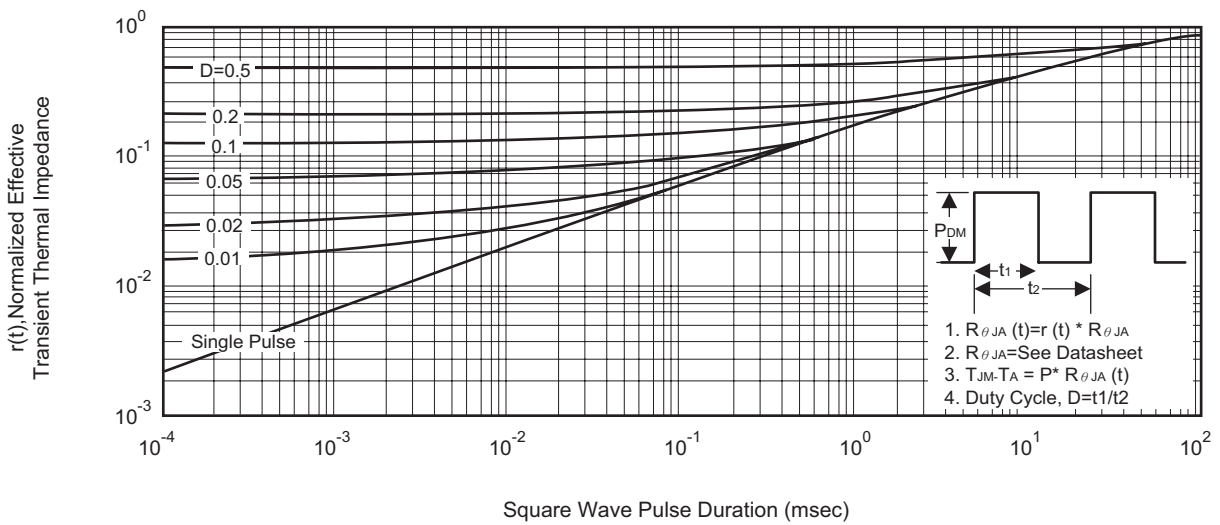
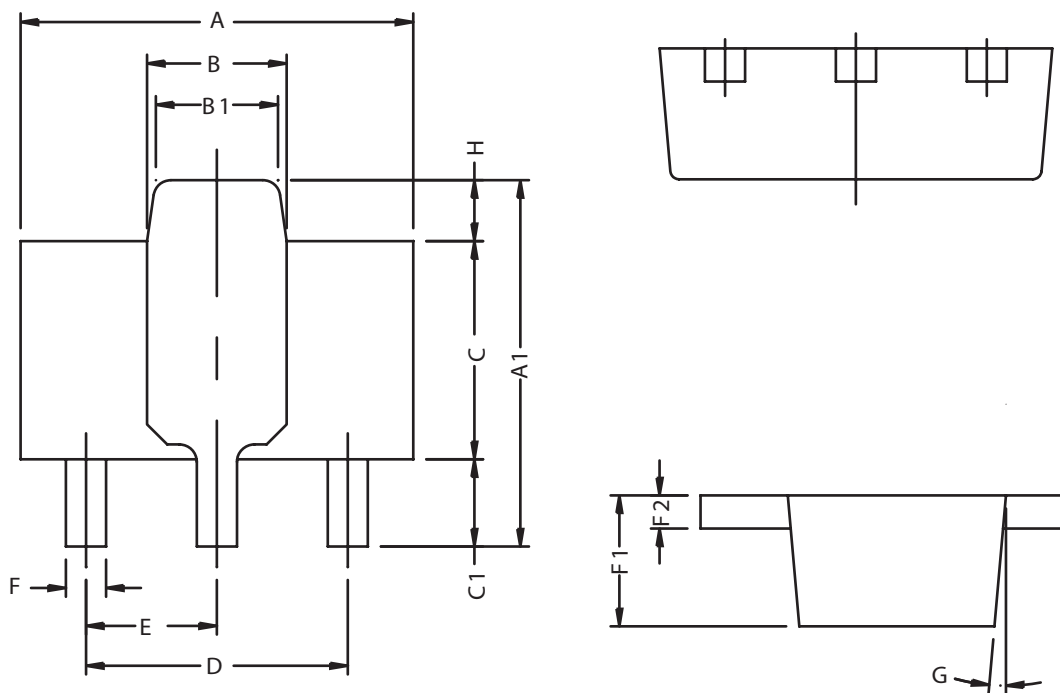


Figure 14. Normalized Thermal Transient Impedance Curve

PACKAGE OUTLINE DIMENSIONS

SOT-89



REF.	DIMENSIONS	
	Milimeters	
	MIN.	MAX.
A	4.40	4.60
A1	4.05	4.25
B	1.50	1.70
B1	1.30	1.50
C	2.40	2.60
C1	0.89	1.20
D	3.00 REF.	
E	1.50 REF.	
F	0.40	0.52
F1	1.40	1.60
F2	0.35	0.41
G	5° TYP.	
H	0.70 REF.	

